

Appl. No. : **10/731,656**
Filed : **December 8, 2003**

REMARKS

Claims 1-25 are pending in the present application and stand rejected on a variety of grounds.

Drawings

As requested by the Examiner, Figure 1 has been amended to include the legend "prior art."

Claim Rejections Under 35 U.S.C. § 112

Claim 5 was rejected under 35 U.S.C. § 112, first paragraph as containing subject matter which was not described in the specification in such a way as to reasonably convey to one of skill in the art at the time the application was filed that the inventors had possession of the claimed invention. In particular, the Examiner found that the original specification does not have support for "n is an integer selected from the group consisting of 1, 2, and 3." Applicants direct the Examiner to paragraph [0040] of the specification which recites "as a nonlimiting example, SiX_n ligands (where $X = \text{F, Cl, Br, or I}$ and $n = 1, 2, \text{ or } 3$) can be formed with a step of exposure to a silicon halide ...". Applicants respectfully submit that this disclosure supports each of the formulas SiX_1 , SiX_2 , and SiX_3 , where $X = \text{F, Cl, Br, or I}$. The fact that the claim is written using Markush language does not change the nature of what is being claimed. As there is sufficient written description support in the specification for $n = 1$, $n = 2$ and $n = 3$, Applicants respectfully request withdrawal of this rejection.

Double-Patenting

Claims 1-25 were rejected under the judicially-created doctrine of obviousness type double-patenting over Claims 1-32 of U.S. Patent No. 6,664,192. Applicants submit herewith a Terminal Disclaimer over U.S. Patent No. 6,664,192. Thus, Applicants request withdrawal of this rejection.

Claim Rejections Under 35 U.S.C. § 103

Claims 1-25 were rejected under 35 U.S.C. § 103(a) as being unpatentable over the Background of the Invention in view of Sneh (U.S. Patent No. 6,200,893).

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With respect to Claim 1, the Examiner found that the Background of the Invention at pages 1-3 discloses a method of selectively depositing a layer on a substrate comprising a first surface and a second surface, the method comprising modifying the first surface and selectively depositing a layer on the second surface relative to the first surface. The Examiner noted that the Background of the Invention fails to teach using an ALD process but found that Sneh makes up for this deficiency.

Applicants respectfully submit that there is no disclosure in the Background of the Invention of a method comprising modifying a first surface and selectively depositing a layer on a second surface relative to the first surface. In addition, there is no disclosure in Sneh that makes up for this deficiency. As a result, Applicants request the withdrawal of the rejection of Claim 1 and Claims 2-7, which depend therefrom.

With respect to Claim 8, the Examiner found that the Background of the Invention at pages 1-3 and Figure 1 disclose a method of selectively depositing a layer on a substrate by modifying a first surface of the substrate to prevent subsequent deposition thereon. The Examiner found that the Background of the Invention fails to teach repeated alternate exposure of the substrate to at least two reactant fluids, but found that this lack of teaching was made up for by Sneh.

Applicants respectfully submit that there is no disclosure in the Background of the Invention of a method of selectively depositing a layer on a substrate by modifying a first surface of the substrate to prevent subsequent deposition of the layer thereon. In addition, there is no teaching in Sneh that makes up for this deficiency. As a result, Applicants request the withdrawal of the rejection of Claim 8 and Claims 9-20 which depend therefrom.

Finally, with respect to Claim 21, the Examiner found that the Background of the Invention discloses a method of selectively blocking formation of a thin film by an ALD process on a first surface compared to a second surface by selectively modifying the first surface. However, the Examiner also states that the background of the invention fails to teach an ALD process utilizing vapor-phase reactants. This deficiency is found to be made up for by Sneh.

There is no disclosure in the Background of the Invention of selectively blocking formation of a thin film on a first surface compared to a second surface. Further, there is no teaching in Sneh that makes up for this deficiency. As a result, the Examiner is respectfully requested to withdraw the rejection of Claims 21-25.

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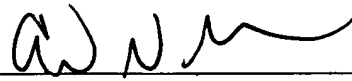
Conclusion

In view of the remarks presented above, Applicants respectfully submit that the present application is in condition for allowance and respectfully requests the same. If any issues remain, the Examiner is cordially invited to contact Applicant's representative at the number provided below in order to resolve such issues promptly.

Respectfully submitted,

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